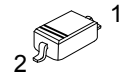


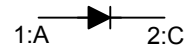
■ PRODUCT CHARACTERISTICS

VR(@IC=100uA)	100V
VF(Typ@IF=250 mA)	1V
IR(@VR=75V)	2uA
IF	150mA

SYMBOL



SOD-123



■ FEATURES

- High breakdown voltage
- Low turn-on voltage
- Guard ring construction for transient protection

■ ABSOLUTE MAXIMUM RATINGS (TA=25°C, unless otherwise specified)

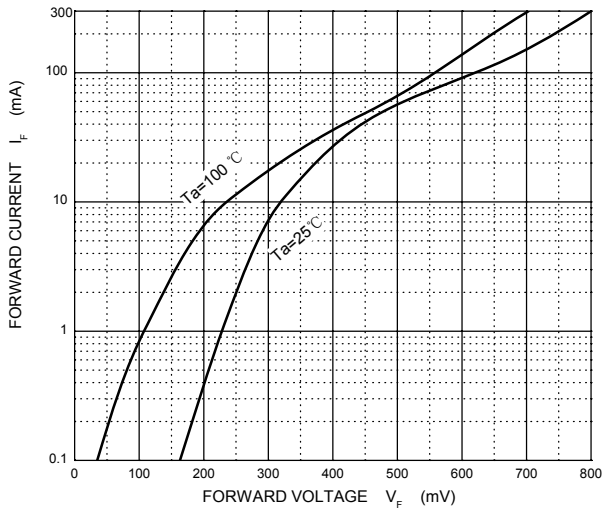
PARAMETER	SYMBOL	RATINGS	UNIT
Peak Repetitive Peak Reverse Voltage	V _{RRM}	100	V
Work Peak Reverse Voltage	V _{RWM}	100	V
Forward continuous Current	I _F	150	mA
Repetitive Peak Forward Current	I _{FRM}	350	mA
Non-repetitive Peak Forward Surge Current@t=8.3ms	I _{FSM}	750	mA
Power Dissipation	P _D	500	mW
Thermal Resistance From Junction to Ambient	R _{θJA}	200	°C/W
Operation Junction Temperature Range	T _J	-40 ~ +125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

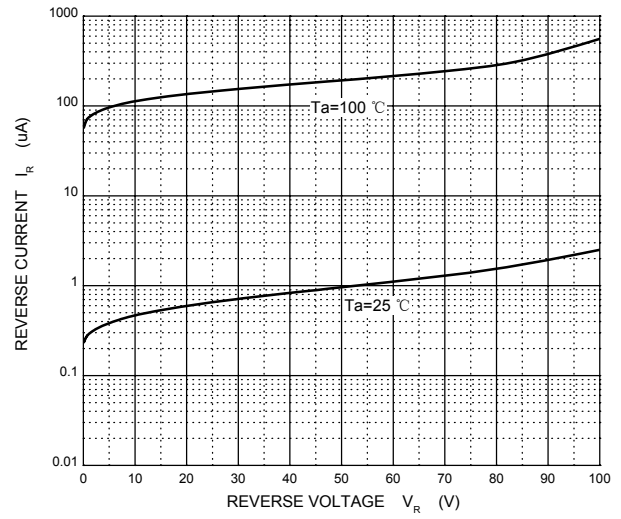
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	V _R	I _R = 100μA	100	-	-	V
Forward Voltage	V _F	I _F =0.1mA	-	-	0.25	V
		I _F =10mA	-	-	0.45	V
		I _F =250mA	-	-	1	V
Reverse Voltage Leakage Current	I _R	V _R =1.5V	-	-	0.3	mA
		V _R =10V	-	-	0.5	μA
		V _R =50V	-	-	1	μA
		V _R =75V	-	-	2	μA
	I _R T _j =60 C	V _R =1.5V	-	-	12	μA
		V _R =10V	-	-	20	μA
		V _R =50V	-	-	44	μA
		V _R =75V	-	-	80	μA
Diode Capacitance	C _T	V _R =0V, f=1.0MHz	-	20	-	pF
		V _R =1V, f=1.0MHz	-	12	-	pF

■ TYPICAL CHARACTERISTICS

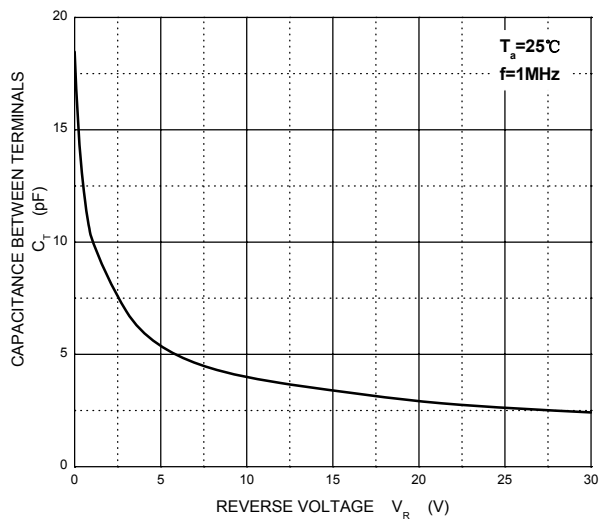
Forward Characteristics



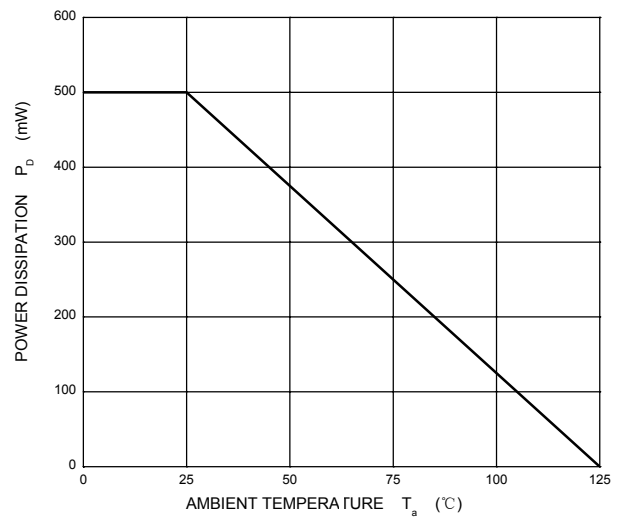
Reverse Characteristics



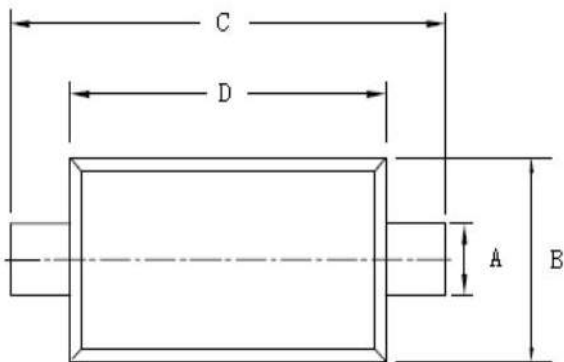
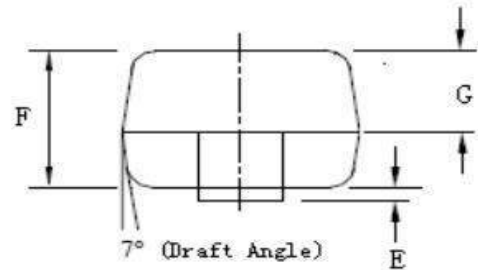
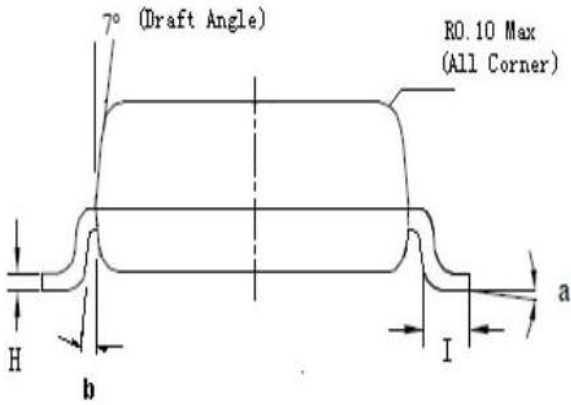
Capacitance Characteristics



Power Derating Curve



■ SOD123 PACKAGE OUTLINE DIMENSIONS



Symbol	Dim in mm		
	Min	Nom	Max
A	0.520	0.550	0.570
B	1.400	1.550	1.700
C	3.550	3.650	3.850
D	2.550	2.650	2.850
E	0.000	0.050	0.100
F	1.050	1.100	1.150
G	0.620	0.650	0.670
H	0.090	0.100	0.110
I	0.250	0.350	0.450
a	0°	-	6°
b	0.4°	-	0.8°